

TECHNICAL DATA

IN74HC138A

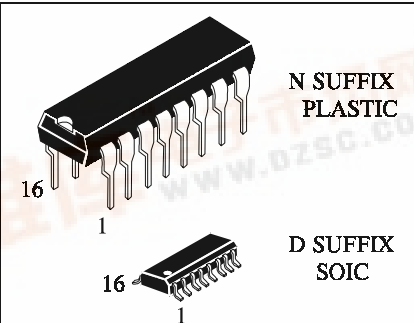
1-of-8 Decoder/Demultiplexer

High-Performance Silicon-Gate CMOS

The IN74HC138A is identical in pinout to the LS/ALS138. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS/ALSTTL outputs.

The IN74HC138A decodes a three-bit Address to one-of-eight active-low outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices



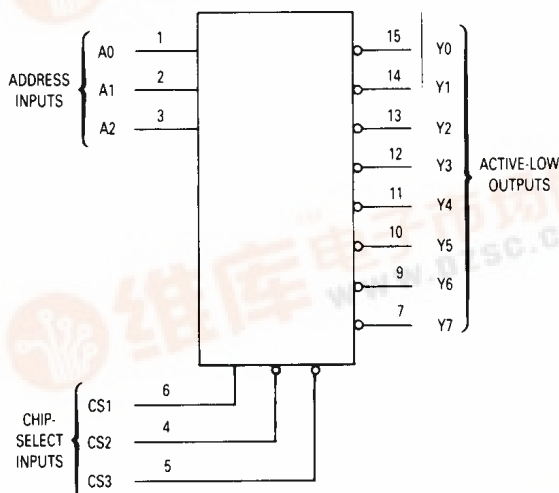
ORDERING INFORMATION

IN74HC138AN Plastic

IN74HC138AD SOIC

 $T_A = -55^\circ$ to 125° C for all packages

LOGIC DIAGRAM



PIN 16 = V_{CC}
PIN 8 = GND

PIN ASSIGNMENT

A0	1	16	V_{CC}
A1	2	15	Y0
A2	3	14	Y1
CS2	4	13	Y2
CS3	5	12	Y3
CS1	6	11	Y4
Y7	7	10	Y5
GND	8	9	Y6

FUNCTION TABLE

Inputs				Outputs							
CS1	CS2	CS3	A2 A1 A0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	H	X X X	H	H	H	H	H	H	H	H
X	H	X	X X X	H	H	H	H	H	H	H	H
L	X	X	X X X	H	H	H	H	H	H	H	H
H	L	L	L L L	L	H	H	H	H	H	H	H
H	L	L	L L H	H	L	H	H	H	H	H	H
H	L	L	L H L	H	H	L	H	H	H	H	H
H	L	L	L H H	H	H	H	L	H	H	H	H
H	L	L	H L L	H	H	H	H	L	H	H	H
H	L	L	H L H	H	H	H	H	H	L	H	H
H	L	L	H H L	H	H	H	H	H	H	L	H
H	L	L	H H H	H	H	H	H	H	H	H	L

H = high level (steady state)

L = low level (steady state)

X = don't care

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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{IN}	DC Input Voltage (Referenced to GND)	-1.5 to V _{CC} +1.5	V
V _{OUT}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
I _{IN}	DC Input Current, per Pin	±20	mA
I _{OUT}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, Plastic DIP+ SOIC Package+	750 500	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package)	260	°C

*Maximum Ratings are those values beyond which damage to the device may occur.
Functional operation should be restricted to the Recommended Operating Conditions.

+Derating - Plastic DIP: - 10 mW/°C from 65° to 125°C
SOIC Package: : - 7 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-55	+125	°C
t _r , t _f	Input Rise and Fall Time (Figure 2) V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{IN} and V_{OUT} should be constrained to the range GND ≤ (V_{IN} or V_{OUT}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}).
Unused outputs must be left open.

DC ELECTRICAL CHARACTERISTICS(Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				25 °C to -55°C	≤85 °C	≤125 °C	
V _{IH}	Minimum High-Level Input Voltage	V _{OUT} =0.1 V or V _{CC} -0.1 V I _{OUT} ≤ 20 µA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{IL}	Maximum Low - Level Input Voltage	V _{OUT} =0.1 V or V _{CC} -0.1 V I _{OUT} ≤ 20 µA	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
V _{OH}	Minimum High-Level Output Voltage	V _{IN} =V _{IH} or V _{IL} I _{OUT} ≤ 20 µA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V _{IN} =V _{IH} or V _{IL} I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
V _{OL}	Maximum Low-Level Output Voltage	V _{IN} =V _{IH} or V _{IL} I _{OUT} ≤ 20 µA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V _{IN} =V _{IH} or V _{IL} I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	
I _{IN}	Maximum Input Leakage Current	V _{IN} =V _{CC} or GND	6.0	±0.1	±1.0	±1.0	µA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{IN} =V _{CC} or GND I _{OUT} =0µA	6.0	4.0	40	160	µA

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AC ELECTRICAL CHARACTERISTICS($C_L=50\text{pF}$, Input $t_r=t_f=6.0\text{ ns}$)

Symbol	Parameter	V _{CC}	Guaranteed Limit			Unit
		V	25 °C to -55°C	≤85°C	≤125°C	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 4)	2.0	135	170	205	ns
		4.5	27	34	41	
		6.0	23	29	35	
t _{PLH} , t _{PHL}	Maximum Propagation Delay , CS1 to Output Y (Figures 2 and 4)	2.0	110	140	165	ns
		4.5	22	28	33	
		6.0	19	24	28	
t _{PLH} , t _{PHL}	Maximum Propagation Delay , CS2 or CS3 to Output Y (Figures 3 and 4)	2.0	120	150	180	ns
		4.5	24	30	36	
		6.0	20	26	31	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0	75	95	110	ns
		4.5	15	19	22	
		6.0	13	16	19	
C _{IN}	Maximum Input Capacitance	-	10	10	10	pF

C _{PD}	Power Dissipation Capacitance (Per Package)	Typical @25°C,V _{CC} =5.0 V			pF
	Used to determine the no-load dynamic power consumption: P _D =C _{PD} V _{CC} ² f+I _{CC} V _{CC}	55			

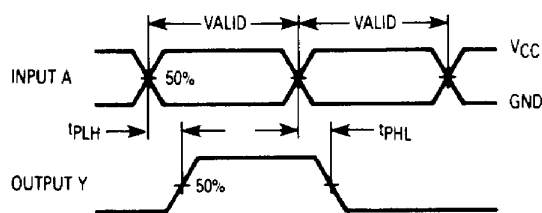


Figure 1. Switching Waveforms

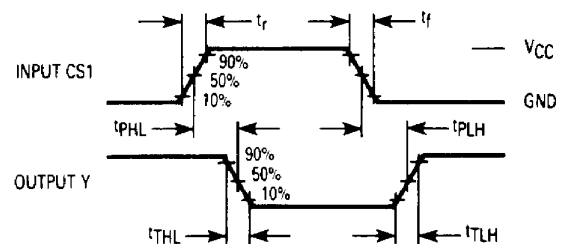


Figure 2. Switching Waveforms

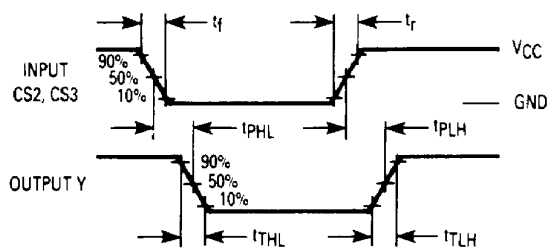
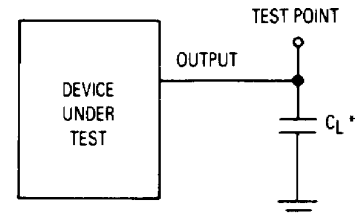


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance.

Figure 4. Test Circuit

EXPANDED LOGIC DIAGRAM

